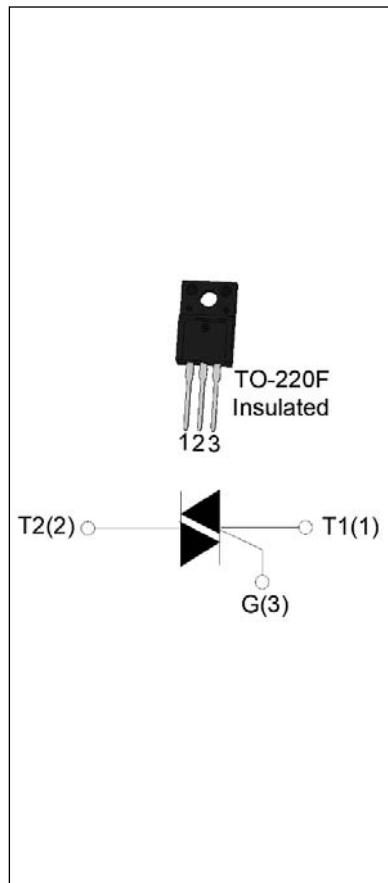


**DESCRIPTION:**

The JST04F-600SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST04F-600SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. By using an external plastic package, JST04F-600SW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\text{ I/II/III}}$	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c \leqslant 97^\circ\text{C}$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	40	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		44	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	8	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	dI/dt	100	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	I - II - III	MAX.	10	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3K\Omega$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	20	mA
		II		35	
I_H	$I_T=100mA$		MAX.	15	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125^\circ C$		MIN.	300	V/ μs
$(dI/dt)c$	$(dV/dt)c=10V/\mu s$, $T_j=125^\circ C$		MIN.	2.5	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$	TYP.	2.5	μs	
t_{off}			25		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit	
V_{TM}	$I_{TM}=5A$	$t_p=380\mu s$	$T_j=25^\circ C$	1.65	V
V_{TO}	Threshold voltage		$T_j=125^\circ C$	0.799	V
R_D	Dynamic resistance		$T_j=125^\circ C$	151	$m\Omega$
I_{DRM}	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}			$T_j=125^\circ C$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	4.5	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ C/W$

ORDERING INFORMATION

<u>J</u>	<u>ST</u>	<u>04</u>	<u>F</u>	<u>-600</u>	<u>SW</u>
JieJie Microelectronics Co., Ltd.					
	Triacs				
		<u>I_T(RMS):4A</u>			
			<u>F:TO-220F(Ins)</u>		<u>SW:IGT1-3≤10mA</u>
				<u>600:V_{DRM}/V_{RRM}≥600V</u>	

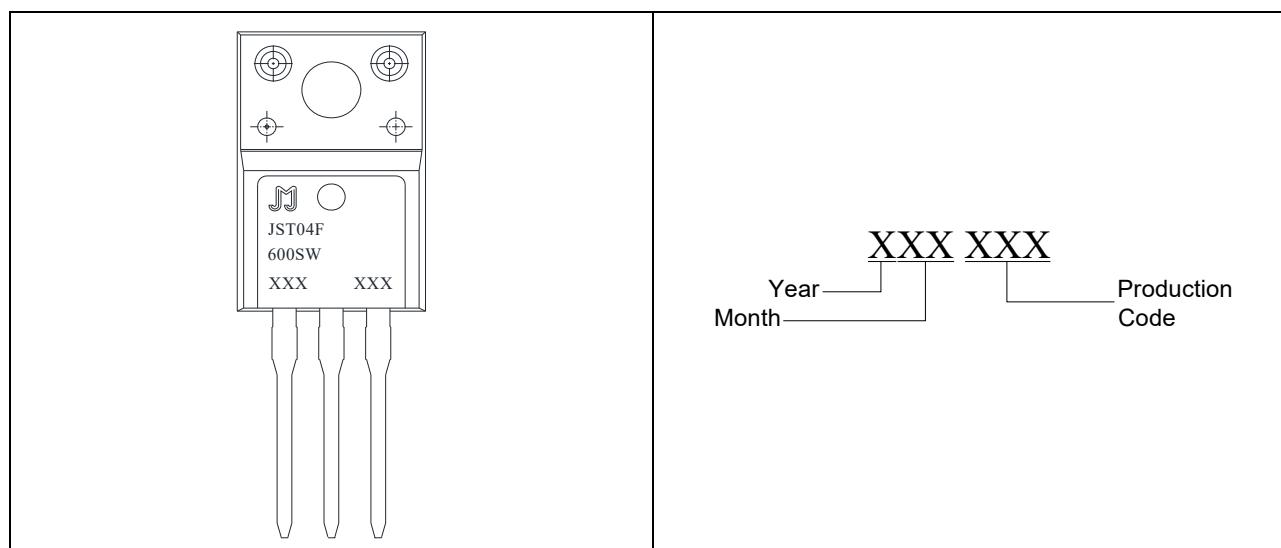
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

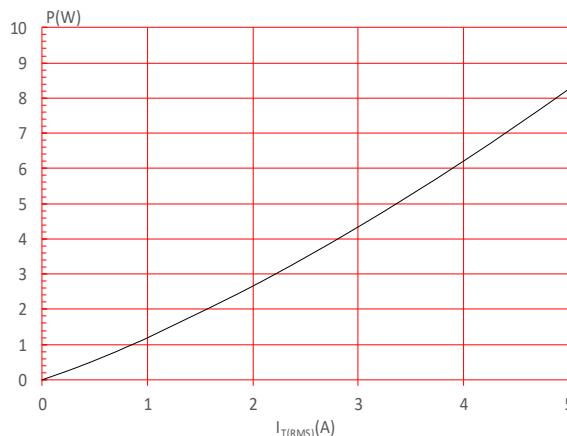


FIG.3: Surge peak on-state current versus number of cycles

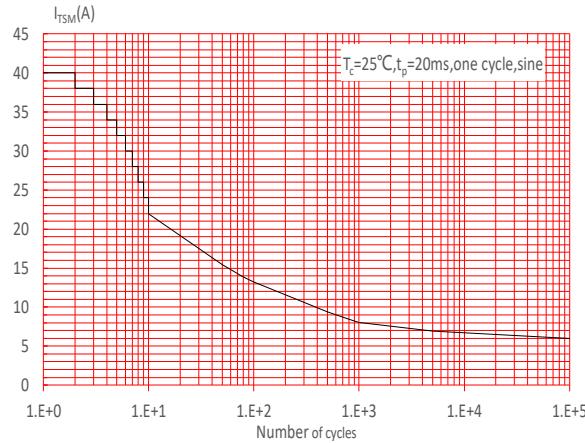


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 100\text{A}/\mu\text{s}$)

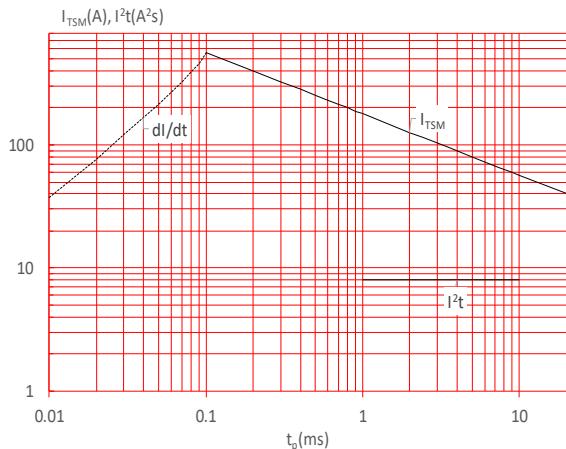


FIG.2: RMS on-state current versus case temperature

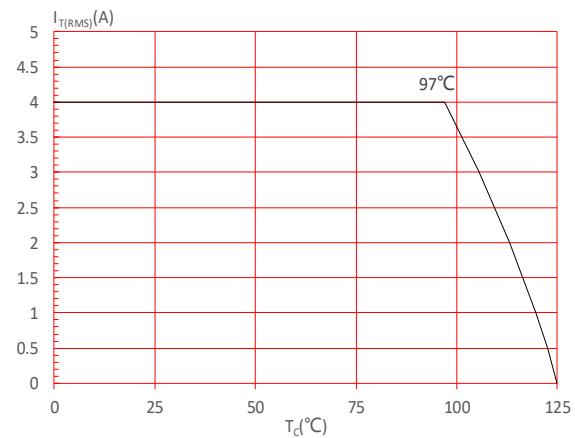


FIG.4: On-state characteristics

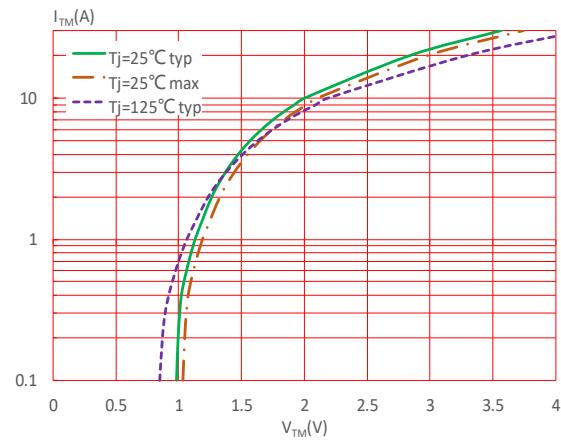


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

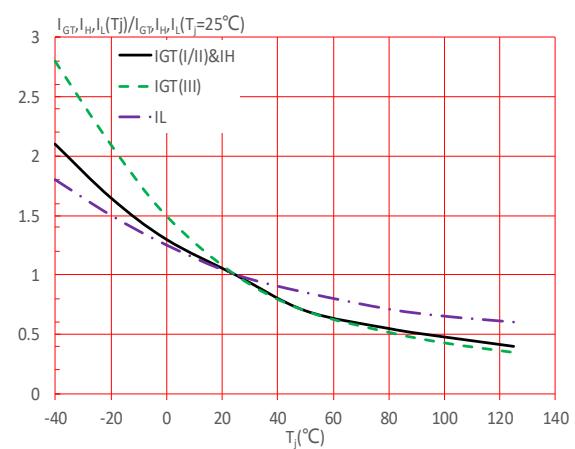
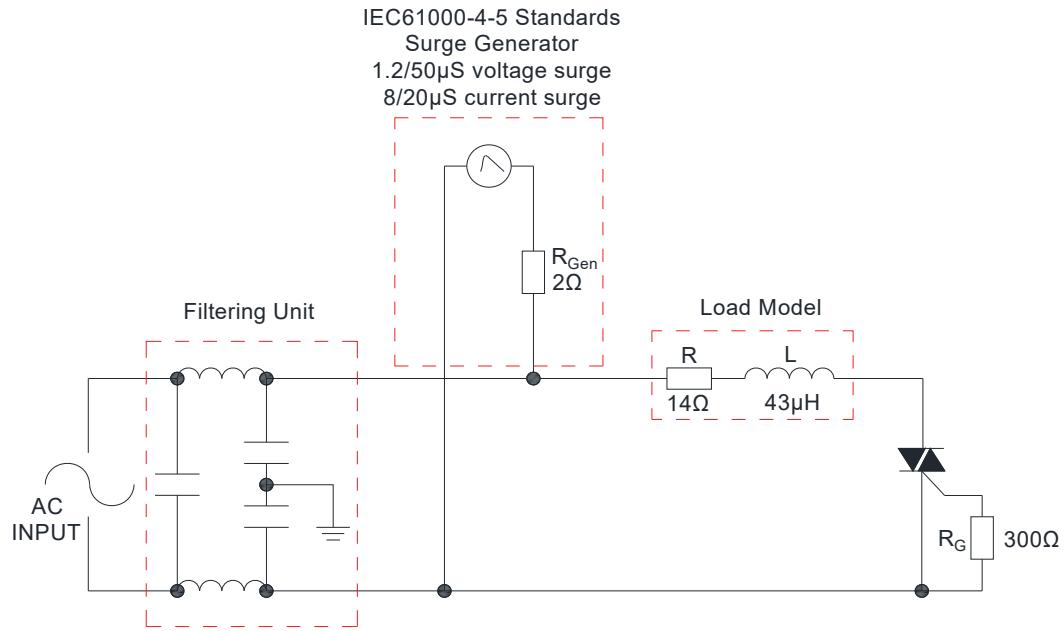


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie Microelectronics

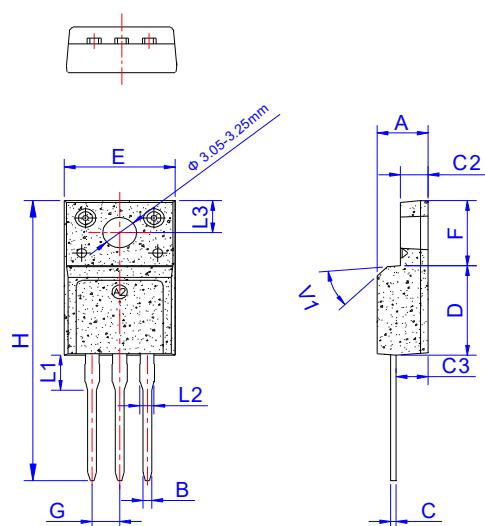
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III			
JST04F-600SW	600	10	TO-220F(Ins)	50	Tube

Document Revision History

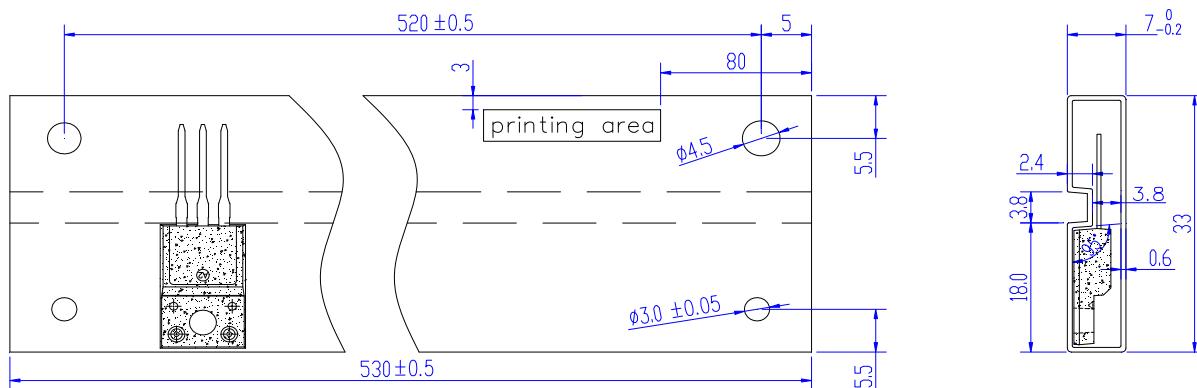
Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Jul.05, 2024	A.1.1	Renew dl/dt

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1			45°			45°

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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